Quad 2-Input Exclusive OR Gate

High-Performance Silicon-Gate CMOS

The MC74HC86A is identical in pinout to the LS86. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

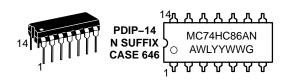
Features

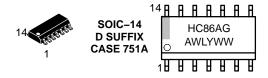
- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with JEDEC Standard No. 7A Requirements
- Chip Complexity: 56 FETs or 14 Equivalent Gates
- Pb-Free Packages are Available*



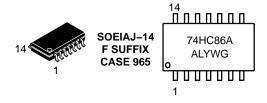
http://onsemi.com

MARKING DIAGRAMS









A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G = Pb−Free Package ■ Pb−Free Package

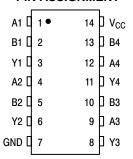
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PIN ASSIGNMENT



FUNCTION TABLE

Inp	Output	
Α	В	Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

LOGIC DIAGRAM

A1
$$\frac{1}{2}$$
 $\frac{3}{10}$ $\frac{3}{10}$ $\frac{3}{10}$ $\frac{3}{10}$ $\frac{3}{10}$ $\frac{3}{10}$ $\frac{4}{10}$ $\frac{6}{10}$ $\frac{8}{10}$ $\frac{8}{10}$ $\frac{3}{10}$ $\frac{11}{10}$ $\frac{3}{10}$ $\frac{11}{10}$ $\frac{3}{10}$ $\frac{11}{10}$ $\frac{3}{10}$ $\frac{11}{10}$ $\frac{11}{10}$ $\frac{3}{10}$ $\frac{11}{10}$ $\frac{11}{$

PIN 14 = V_{CC}

PIN 7 = GND

 $Y = A \oplus B$

 $= \overline{A}B + A\overline{B}$

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC86AN	PDIP-14	500 Units / Rail
MC74HC86ANG	PDIP-14 (Pb-Free)	500 Units / Rail
MC74HC86AD	SOIC-14	55 Units / Rail
MC74HC86ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HC86ADR2	SOIC-14	2500 Units / Reel
MC74HC86ADR2G	SOIC-14 (Pb-Free)	2500 Units / Reel
MC74HC86ADTR2	TSSOP-14*	2500 Units / Reel
MC74HC86ADTR2G	TSSOP-14*	2500 Units / Reel
MC74HC86AF	SOEIAJ-14	50 Units / Rail
MC74HC86AFG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74HC86AFEL	SOEIAJ-14	2000 Units / Reel
MC74HC86AFELG	SOEIAJ-14 (Pb-Free)	2000 Units / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb–Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $V_{\rm CC}$). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
Vcc	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Reference GND)			V _{CC}	V
T _A	Operating Temperature, All Package Types		- 55	+ 125	°C
t _r , t _f	(Figure 1) V _{CC}	= 2.0 V = 4.5 V = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC} V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V _{OH}	Minimum High–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{split} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & I_{\text{out}} \leq 2.4 \text{ mA} \\ I_{\text{out}} \leq 4.0 \text{ mA} \\ I_{\text{out}} \leq 5.2 \text{ mA} \end{split}$	4.5	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} \qquad \begin{aligned} I_{\text{out}} &\leq 2.4 \text{ mA} \\ I_{\text{out}} &\leq 4.0 \text{ mA} \\ I_{\text{out}} &\leq 5.2 \text{ mA} \end{aligned}$	4.5	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	v _{cc} v	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	1.0	10	40	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \ pF$, Input t, = $t_f = 6 \ ns$)

			Gu	Guaranteed Limit		
Symbol	Parameter	v _{cc}	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{PLH} ,	Maximum Propagation Delay, Input A or B to Output Y	2.0	100	125	150	ns
t _{PHL}	(Figures 1 and 2)	3.0	80	90	110	
		4.5	20	25	31	
		6.0	17	21	26	
t _{TLH} ,	Maximum Output Transition Time, Any Output	2.0	75	95	110	ns
t _{THL}	(Figures 1 and 2)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
C _{in}	Maximum Input Capacitance	_	10	10	10	pF

NOTES:

- 1. For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).
- 2. Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C_PD	Power Dissipation Capacitance (Per Gate)*	33	pF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

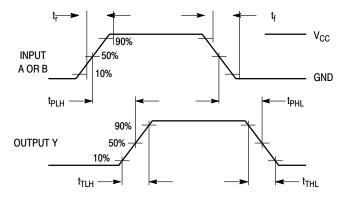
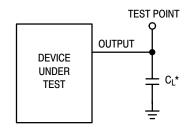


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance

Figure 2. Test Circuit

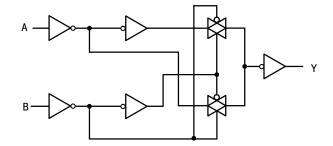
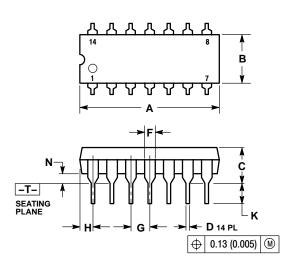
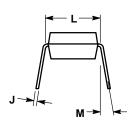


Figure 3. Expanded Logic Diagram (1/4 of Device)

PACKAGE DIMENSIONS

PDIP-14 **N SUFFIX** CASE 646-06 ISSUE N





NOTES:

- NOTES:

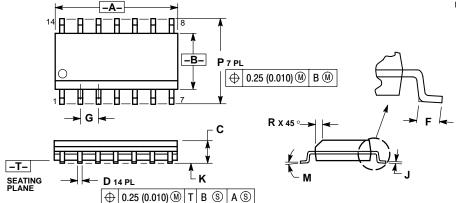
 1. DIMENSIONING AND TOLERANCING
 PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION L TO CENTER OF LEADS
 WHEN FORMED PARALLEL.
- VITEN FORWED FARALLEL.
 DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 ROUNDED CORNERS OPTIONAL.

	INCHES MILLIMETE			IFTFRS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	18.80
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M		10 °		10 °
N	0.015	0.039	0.38	1.01

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE G**



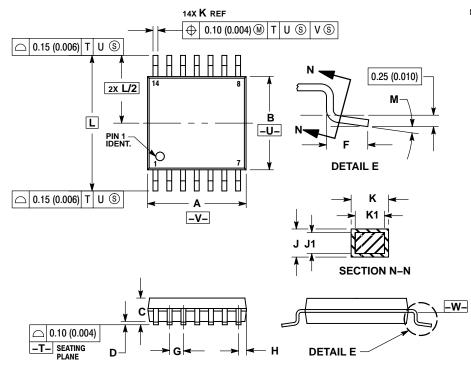
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- 4. MAAIMUM MOLD PROTRUSION 0.15 (0.0)
 PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.127
 (0.005) TOTAL IN EXCESS OF THE D
 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE A**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 - DIMENSION AT MAXIMUM MATERIAL CONDITION.

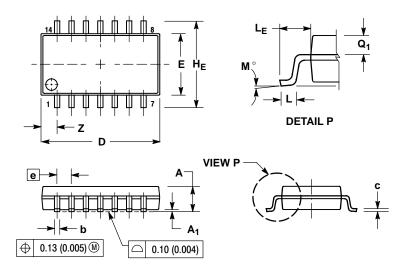
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
М	0 °	8 °	0 °	8 °

PACKAGE DIMENSIONS

SOEIAJ-14 **F SUFFIX** CASE 965-01 **ISSUE O**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	MILLIMETERS INC		HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		1.42		0.056

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